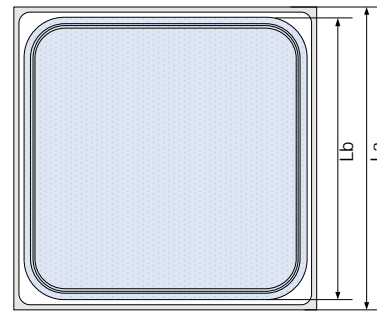


**2SB267100MA LOW IR SCHOTTKY BARRIER DIODE CHIPS**
**DESCRIPTION**

- ∅ 2SB267100MA is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- ∅ Due to special schottky barrier structure, the chips have very low reverse leakage current ( typical  $I_R=0.002\text{mA}@V_r=100\text{V}$  ) and maximum 150°C operation junction temperature;
- ∅ Low power losses, high efficiency;
- ∅ Guard ring construction for transient protection;
- ∅ High ESD capability;
- ∅ High surge capability;
- ∅ Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- ∅ Chip Size: 2670 $\mu\text{m}$  X 2670 $\mu\text{m}$ ;
- ∅ Chip Thickness: 280 $\pm$ 20 $\mu\text{m}$ ;
- ∅ Have two top side electrode materials for customer to choose, detail refer to ordering specifications.


**Chip Topography and Dimensions**

 La: Chip Size: 2670 $\mu\text{m}$ ;

 Lb: Pad Size: 2470 $\mu\text{m}$ ;

**ORDERING SPECIFICATIONS**

Product Name	Specification
2SB267100MAYY	For Axial leads package
2SB267100MAYL	For Au and AISi wire bonding package

**ABSOLUTE MAXIMUM RATINGS**

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	100	V
Average Forward Rectified Current	IFAV	10	A
Peak Forward Surge Current@8.3ms	IFSM	150	A
Maximum Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-40~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C)**

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=0.5mA	100	--	V
Forward Voltage	VF	IF=10A	--	0.85	V
Reverse Current	IR	VR=100V	--	0.5	mA